



NPN AVALANCHE TRANSISTOR IN SOT23

Features

- Avalanche Transistor
- 60A Peak Avalanche Current (Pulse width = 20ns)
- BV_{CES} > 260V (415) & 320V (417)
- BV_{CEO} > 100V
- Specifically designed for Avalanche mode operation
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

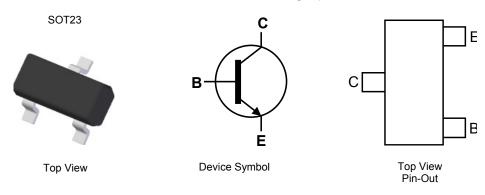
The FMMT415/417 are NPN silicon planar bipolar transistors designed for operating in avalanche mode. Tight process control and low inductance packaging combine to produce high current pulses with fast edges.

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

Applications

- Laser Diode Drivers for Ranging and Measurement (LIDAR)
- Automotive Radar Systems
 - Adaptive Cruise Control
 - Collision Avoidance System
- Fast Edge Switch Generator
- High Speed Pulse Generators



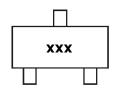
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT415TD	AEC-Q101	415	7	8	500
FMMT417TD	AEC-Q101	417	7	8	500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



xxx = Product Type Marking Code (See Ordering Information)



FMMT415 FMMT417

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	FMMT415	FMMT417	Unit
Collector-Base Voltage	V _{CBO}	260	320	V
Collector-Emitter Voltage	V _{CES}	260	320	V
Collector-Emitter Voltage	V _{CEO}	100	100	V
Emitter-Base Voltage	V _{EBO}	6		V
Continuous Collector Current	Ic	500		mA
Peak Collector Current (Pulse Width = 20ns)	I _{CM}	60		Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_{D}	500	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead (Note 6)		R ₀ JL	197	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

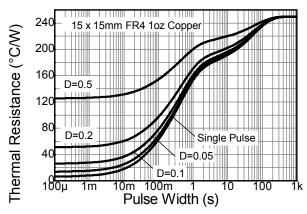
^{5.} For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{6.} Thermal resistance from junction to solder-point (at the end of the collector lead).

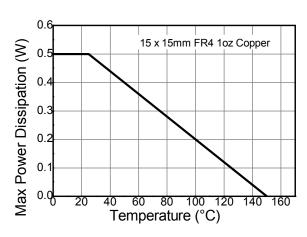
^{7.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



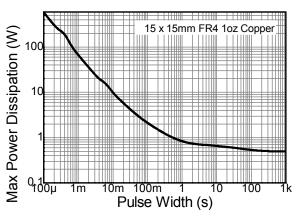
Thermal Characteristics and Derating Information



Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



FMMT415 **FMMT417**

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage	FMMT415	BV _{CES}	260	_	_	V	I _C = 1mA T _J = -55 to +150°C
	FMMT417		320	_	_		I _C = 1mA
Collector-Emitter Breakdown Voltage (Note 8)		BV _{CEO}	100	_	_	V	I _C = 100μA
Emitter-Base Breakdown Voltage		BV _{EBO}	6	_	_	V	I _E = 100μA
Collector Cutoff Current		I _{CBO}	_	_	100 10	nΑ μΑ	V _{CB} = 180V V _{CB} = 180V, T _J = +100°C
Emitter Cutoff Current		I _{EBO}	_	_	100	nA	V _{EB} = 4V
Static Forward Current Transfer Ratio (Note 8)		h _{FE}	25	_	_		I _C = 10mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 8)		V _{CE(sat)}	_	_	500	mV	I _C = 10mA, I _B = 1mA
Base-Emitter Saturation Voltage (Note 8)		V _{BE(sat)}	_	_	900	mV	I _C = 10mA, I _B = 1mA
Pulsed Current in Second Breakdown		lusB	15 25		_	A A	$V_C = 200V, C_{CE} = 620pF$ $V_C = 250V, C_{CE} = 620pF$
Collector-emitter inductance		L _{ce}	_	2.5	_	nΗ	Standard SOT23 leads
Output Capacitance		C _{obo}			8	pF	V _{CB} = 20V, I _E = 0 f = 100MHz
Transition Frequency		f _T	40	_	_	MHz	V _{CE} = 20V, I _C = 10mA, f = 20MHz

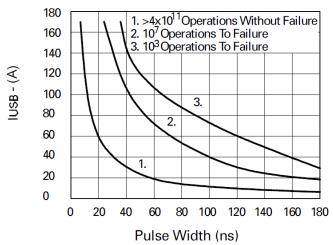
Note:

8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

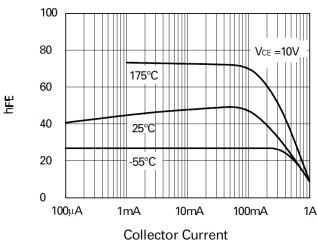




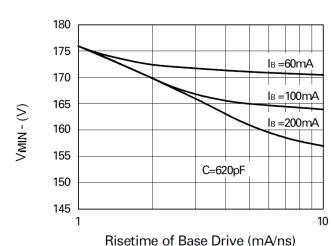




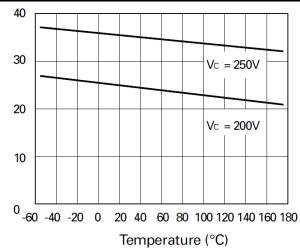
Maximum Avalanche Current v Pulse Width



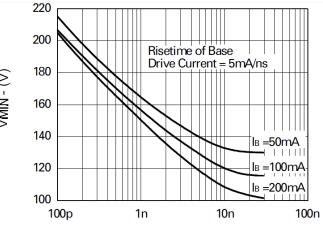
hfe v IC



Minimum starting voltage as a function of drive current

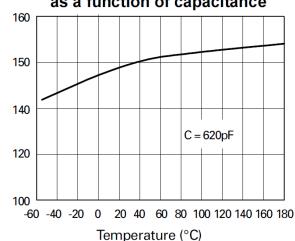


IUSB v Temperature for the specified conditions



Collector-Emitter Capacitance (F)

Minimum starting voltage as a function of capacitance

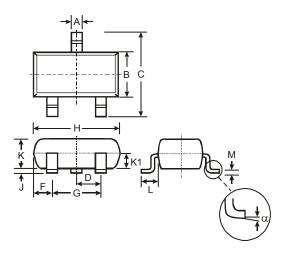


Minimum starting voltage as a function of temperature



Package Outline Dimensions

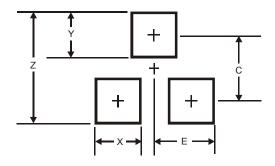
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Y	0.9		
С	2.0		
E	1.35		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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